

### Höchstzulässige Werte / Maximum rated values

#### Elektrische Eigenschaften / Electrical properties

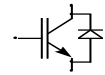
Kollektor-Emitter-Sperrspannung collector-emitter voltage		$V_{CES}$	1700	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ\text{C}$	$I_{C,nom.}$	150	A
	$T_C = 25^\circ\text{C}$	$I_C$	300	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^\circ\text{C}$	$I_{CRM}$	300	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$ , Transistor	$P_{tot}$	1250	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		$V_{GES}$	+/- 20V	V
Dauergleichstrom DC forward current		$I_F$	150	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	$I_{FRM}$	300	A
Grenzlastintegral der Diode $I^2t$ - value, Diode	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	$I^2t$	4.500	$\text{A}^2\text{s}$
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	$V_{ISOL}$	3,4	kV

### Charakteristische Werte / Characteristic values

#### Transistor / Transistor

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 150\text{A}, V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	2,6	3,2	V
	$I_C = 150\text{A}, V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}$		-	3,1	3,6	V
Gate-Schwellenspannung gate threshold voltage	$I_C = 7\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$	$Q_G$	-	1,8	-	$\mu\text{C}$
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{ies}$	-	10	-	nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{res}$	-	0,5	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}$	$I_{CES}$	-	0,05	0,3	mA
	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}$		-	4		mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	$I_{GES}$	-	-	200	nA

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**Charakteristische Werte / Characteristic values**

**Transistor / Transistor**

**min. typ. max.**

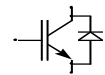
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_{d,on}$	-	0,1	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 25^\circ C$		-	0,1	-	$\mu s$
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_r$	-	0,1	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$		-	0,1	-	$\mu s$
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_{d,off}$	-	0,8	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$		-	0,9	-	$\mu s$
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_f$	-	0,03	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$		-	0,03	-	$\mu s$
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 150A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 10\Omega, T_{vj} = 125^\circ C, L_S = 60nH$	$E_{on}$	-	70	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 150A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 10\Omega, T_{vj} = 125^\circ C, L_S = 60nH$	$E_{off}$	-	46	-	mWs
Kurzschlußverhalten SC Data	$t_p \leq 10\mu sec, V_{GE} \leq 15V$ $T_{vj} \leq 125^\circ C, V_{CC} = 1000V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$I_{SC}$	-	600	-	A
Modulinduktivität stray inductance module		$L_{sCE}$	-	30	-	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	pro Zweig / per arm	$R_{CC+EE}$	-	0,6	-	m $\Omega$

**Charakteristische Werte / Characteristic values**

**Diode / Diode**

**min. typ. max.**

Durchlaßspannung forward voltage	$I_F = 150A, V_{GE} = 0V, T_{vj} = 25^\circ C$	$V_F$	-	2,1	2,5	V
	$I_F = 150A, V_{GE} = 0V, T_{vj} = 125^\circ C$		-	2,1	2,5	V
Rückstromspitze peak reverse recovery current	$I_F = 150A, -di_F/dt = 1700A/\mu sec$	$I_{RM}$	-	110	-	A
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$		-	130	-	A
Sperrverzögerungsladung recovered charge	$I_F = 150A, -di_F/dt = 1700A/\mu sec$	$Q_r$	-	35	-	$\mu As$
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$		-	60	-	$\mu As$
Abschaltenergie pro Puls reverse recovery energy	$I_F = 150A, -di_F/dt = 1700A/\mu sec$	$E_{rec}$	-	15	-	
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$		-	30	-	mWs



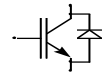
### Thermische Eigenschaften / Thermal properties

			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor / transistor, DC	$R_{thJC}$	-	-	0,1	K/W
	Diode/Diode, DC		-	-	0,24	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{Paste} = 1 \text{ W/m}^2\text{K}$ / $\lambda_{grease} = 1 \text{ W/m}^2\text{K}$	$R_{thCK}$	-	-	0,012	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj}$	-	-	150	°C
Betriebstemperatur operation temperature		$T_{op}$	-40	-	125	°C
Lagertemperatur storage temperature		$T_{stg}$	-40	-	125	°C

### Mechanische Eigenschaften / Mechanical properties

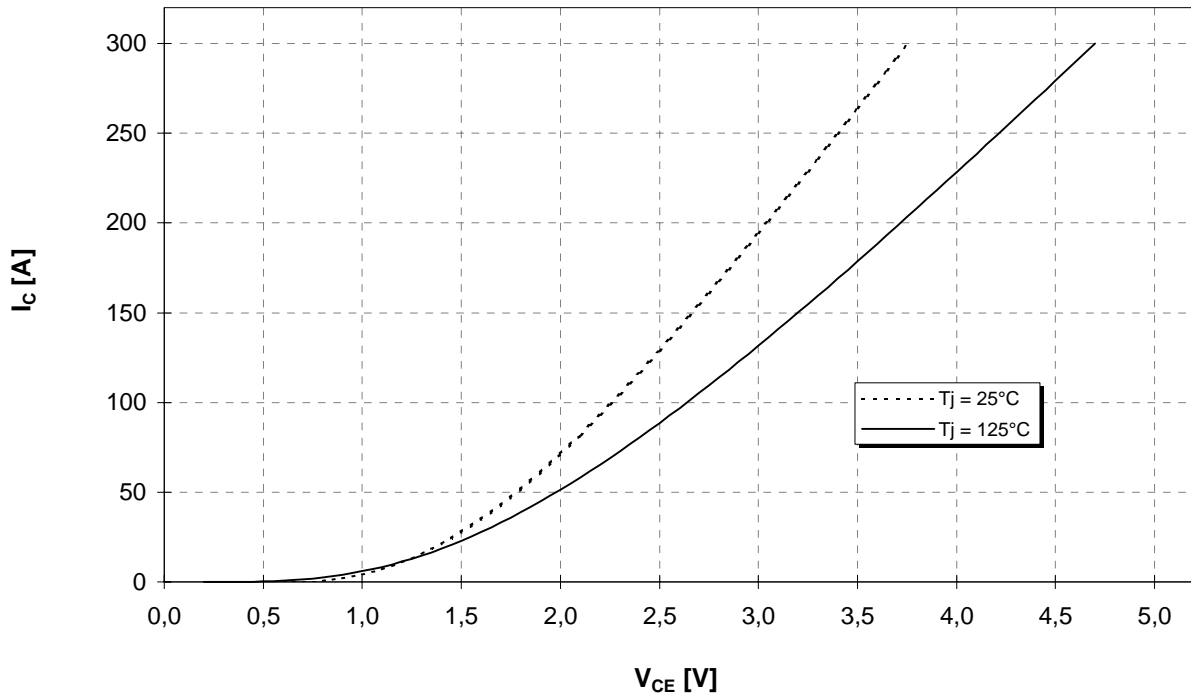
Gehäuse, siehe Anlage case, see appendix					
Innere Isolation internal insulation				$\text{Al}_2\text{O}_3$	
Kriechstrecke creepage distance				20	mm
Luftstrecke clearance				11	mm
CTI comperative tracking index					
Anzugsdrehmoment f. mech. Befestigung mounting torque		max.		5	Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	terminals M6	max.		5	Nm
Gewicht weight		G		340	g

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.  
This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



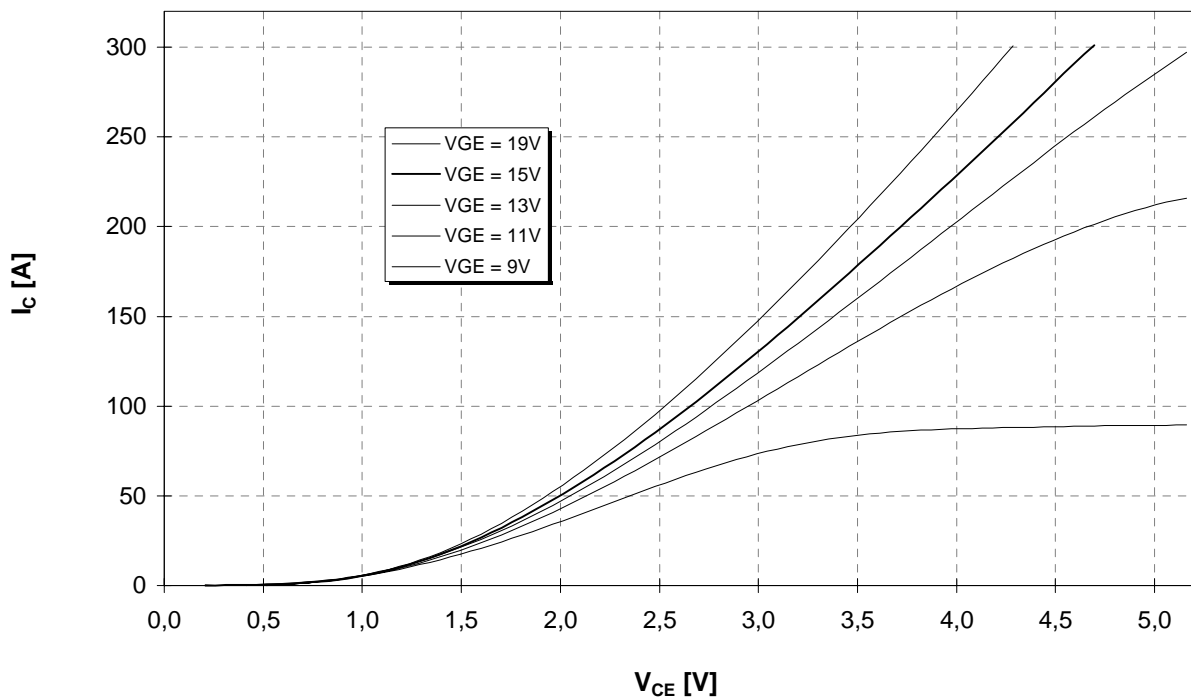
**Ausgangskennlinie (typisch)**  
**Output characteristic (typical)**

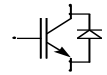
$I_C = f(V_{CE})$   
 $V_{GE} = 15V$



**Ausgangskennlinienfeld (typisch)**  
**Output characteristic (typical)**

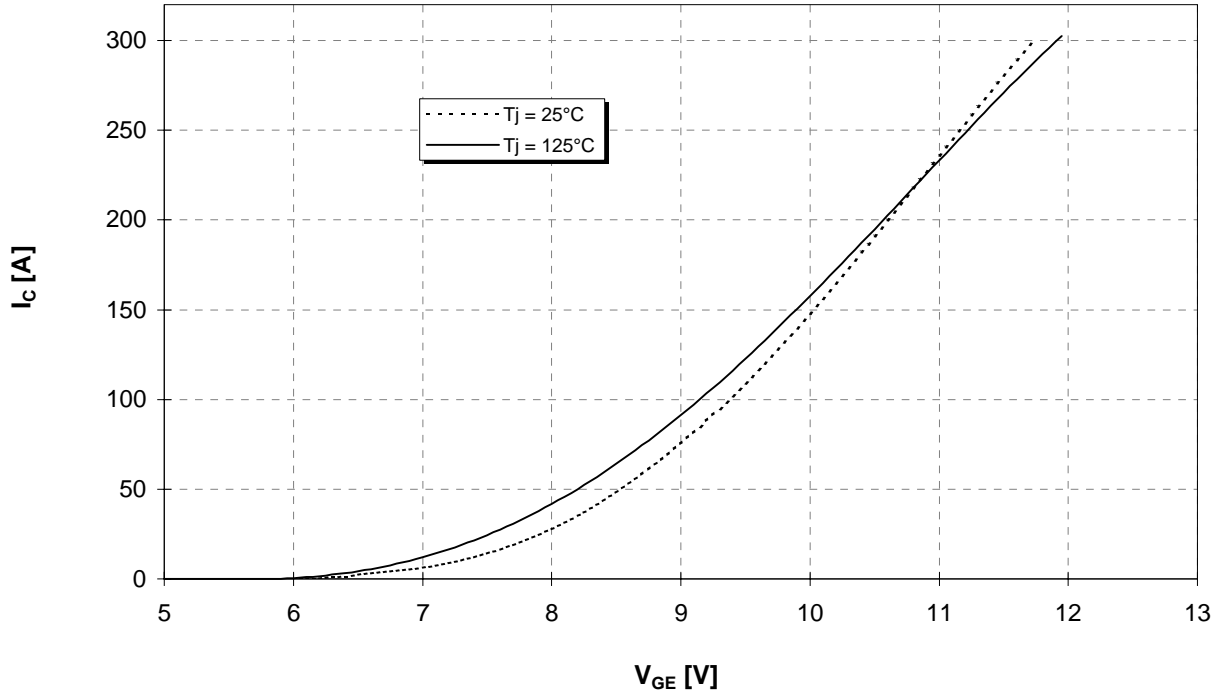
$I_C = f(V_{CE})$   
 $T_{vj} = 125°C$





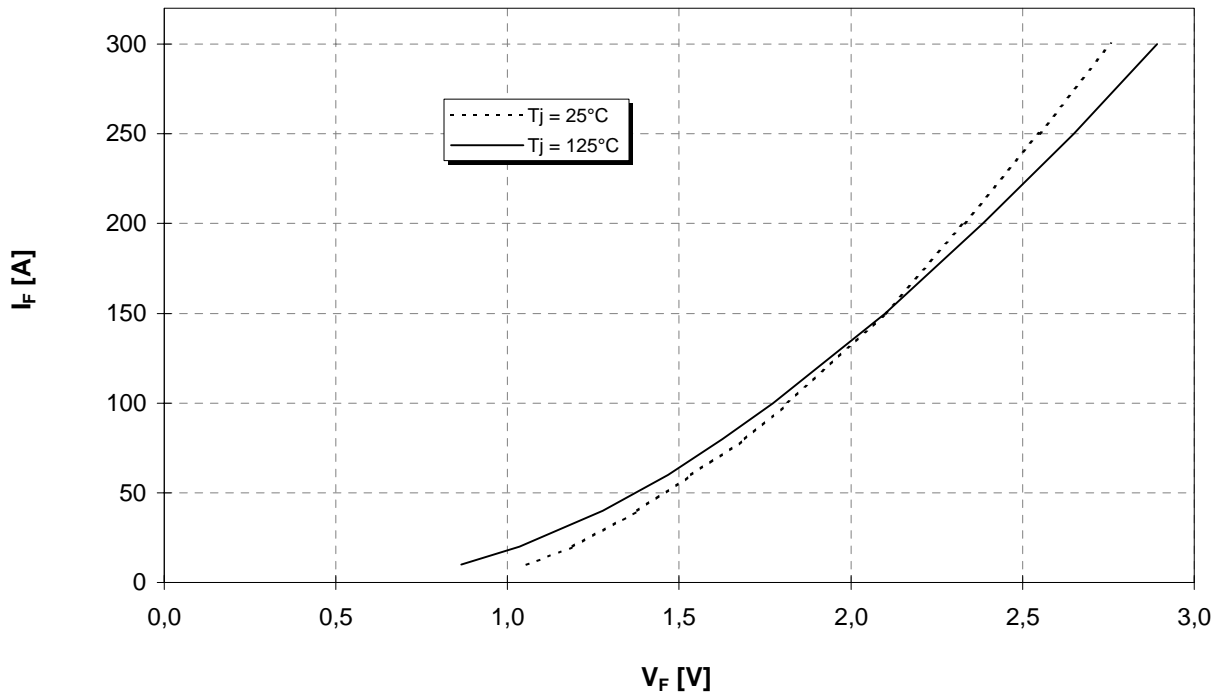
**Übertragungscharakteristik (typisch)**  
**Transfer characteristic (typical)**

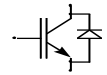
$I_C = f(V_{GE})$   
 $V_{CE} = 20V$



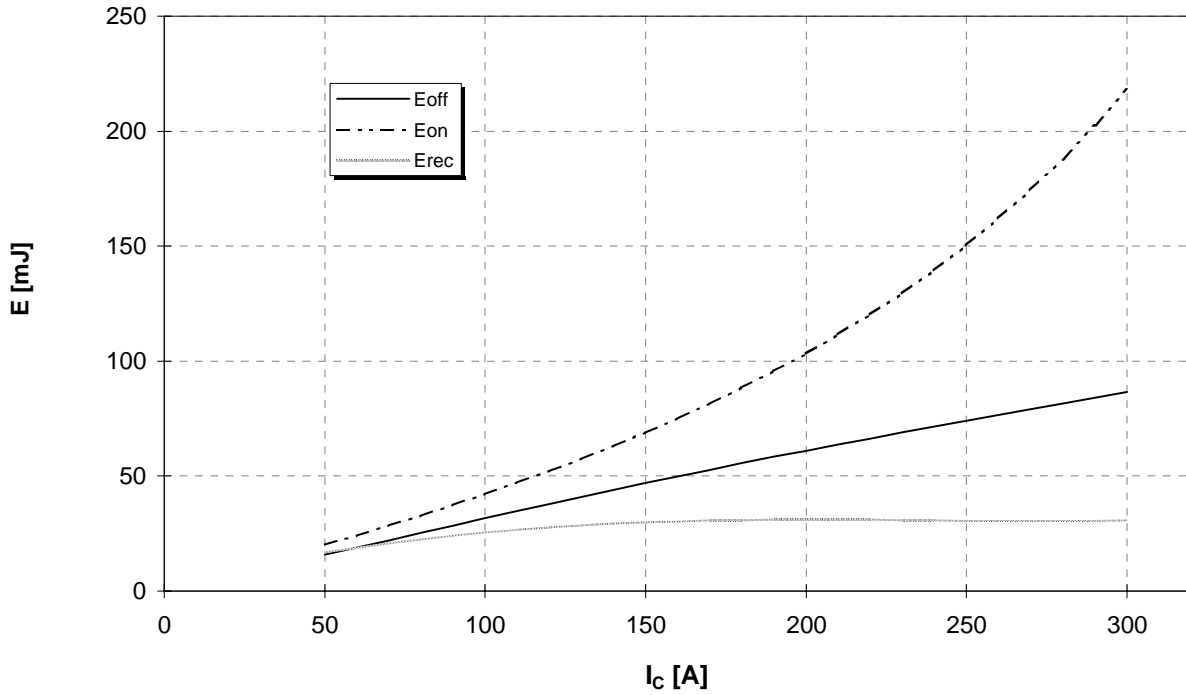
**Durchlaßkennlinie der Inversdiode (typisch)**  
**Forward characteristic of inverse diode (typical)**

$I_F = f(V_F)$

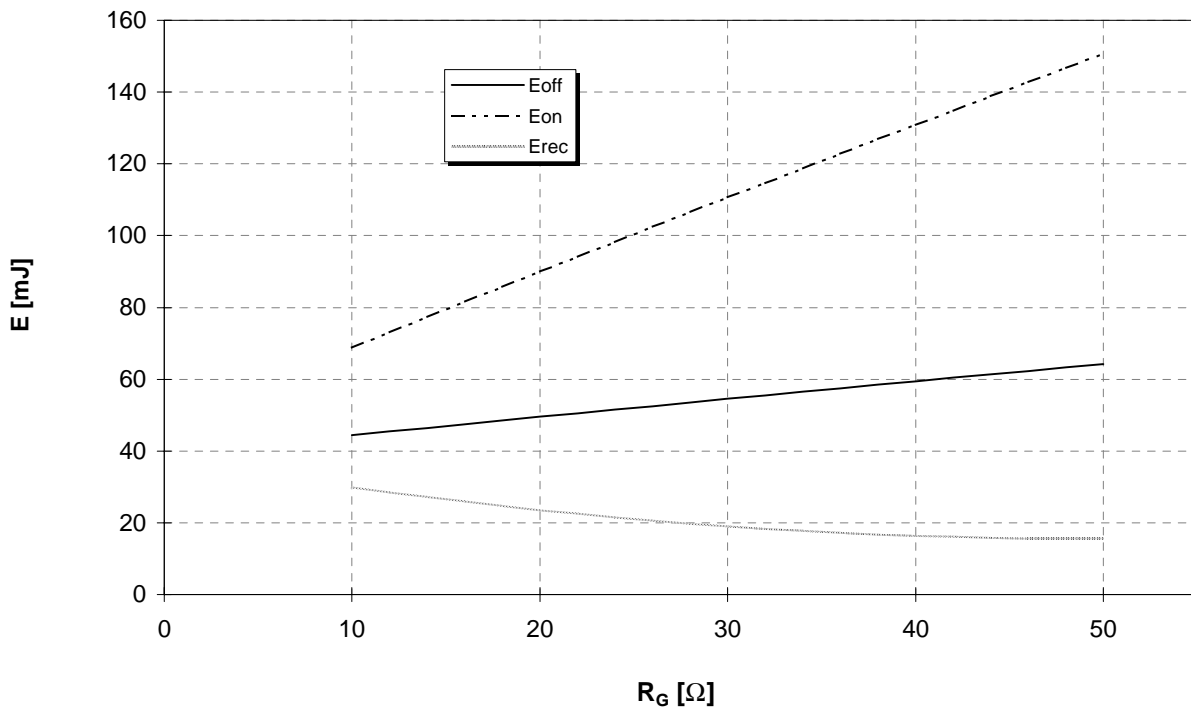


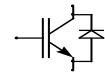


**Schaltverluste (typisch)  $E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$ ,  $E_{rec} = f(I_C)$**   
**Switching losses (typical)  $R_{gon} = R_{goff} = 10\Omega$ ,  $V_{CE} = 900V$ ,  $T_j = 125^\circ C$**



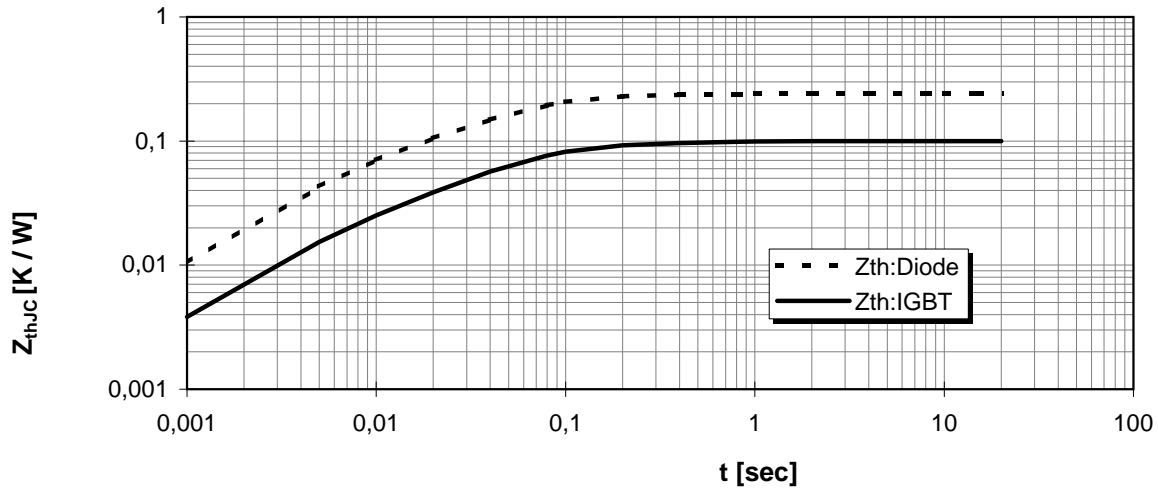
**Schaltverluste (typisch)  $E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$ ,  $E_{rec} = f(R_G)$**   
**Switching losses (typical)  $I_C = 150A$ ,  $V_{CE} = 900V$ ,  $T_j = 125^\circ C$**





**Transienter Wärmewiderstand**  
**Transient thermal impedance**

$Z_{thJC} = f(t)$

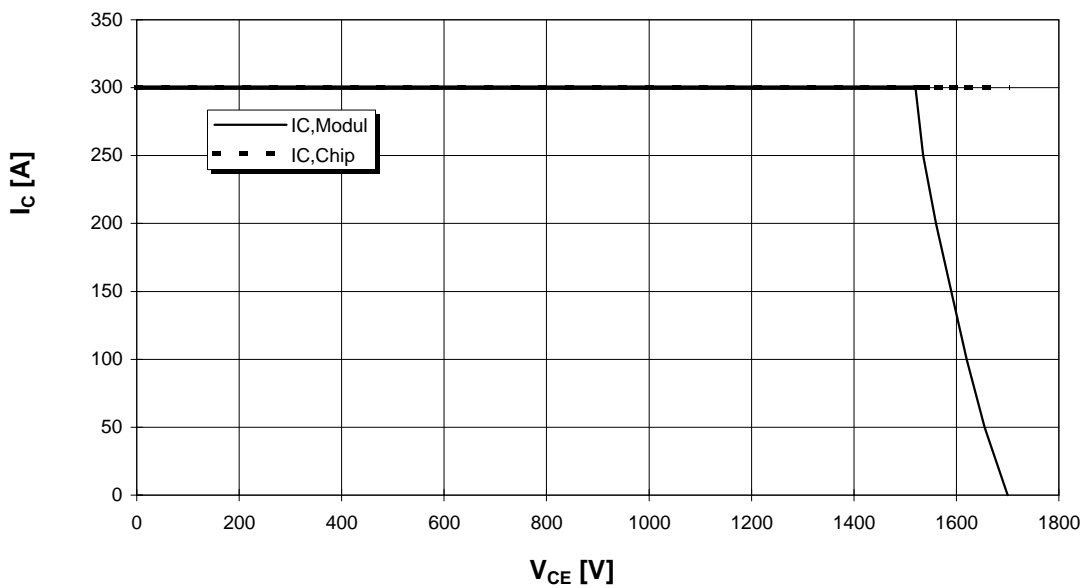


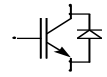
i		1	2	3	4
$r_i$ [K/kW]	: IGBT	11,16	32,28	48,09	8,47
$\tau_i$ [sec]	: IGBT	0,0047	0,0356	0,0613	0,4669
$r_i$ [K/kW]	: Diode	44,67	88,51	88,51	18,32
$\tau_i$ [sec]	: Diode	0,0062	0,0473	0,0473	0,2322

**Sicherer Arbeitsbereich (RBSOA)**

**Reverse bias safe operation area (RBSOA)**

$R_g = 10 \text{ Ohm}, T_{vj} = 125^\circ\text{C}$





**vorläufige Daten**  
**preliminary data**

